

FEATURES :

High efficiency GaAsP/GaP orange chip (MO1288A/C)
and GaP/GaP green chip (MG1288A/C)
Anode column, Cathode row (with suffix A);
Cathode column, Anode row (with suffix C)
High contrast
Wide viewing angle
8 x 8 matrix array with row-column select
Regged encapsulation (Filled reflector construction)
End & side stackable

ABSOLUTE MAXIMUM RATINGS

Power Dissipation / Dot	75mW
Peak Forward Current / Dot*	100mA
Continuous Forward Current / Dot	25mA
Reverse Voltage / Dot	5V
Operating Temperature Range	-25 to +80°C
Storage Temperature Range	-20 to +75°C
Lead Temperature (Soldering 5 sec., 1/16" from body)	260°C

* Note : Pulse Width = 1mS, Duty Ratio = 1/10.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER		SYMBOL	MO1288	MG1288	UNIT	CONDITIONS
Forward Voltage	MAX	VF	3.0	3.0	V	IF=20mA
Luminous Intensity	MIN	IV	1.5	1.8	mcd	IF=10mA
	TYP		2.2	3.0	mcd	
Dot to Dot Luminous Intensity Ratio	MAX		2:1	2:1		IF=10mA
Reverse Current Any Bar	MAX	IR	100	100	μA	VR=5V
Peak Wavelength	TYP	λp	630	565	nm	IF=20mA
Spectral Line Half Width	TYP	Δλ	40	30	nm	IF=20mA



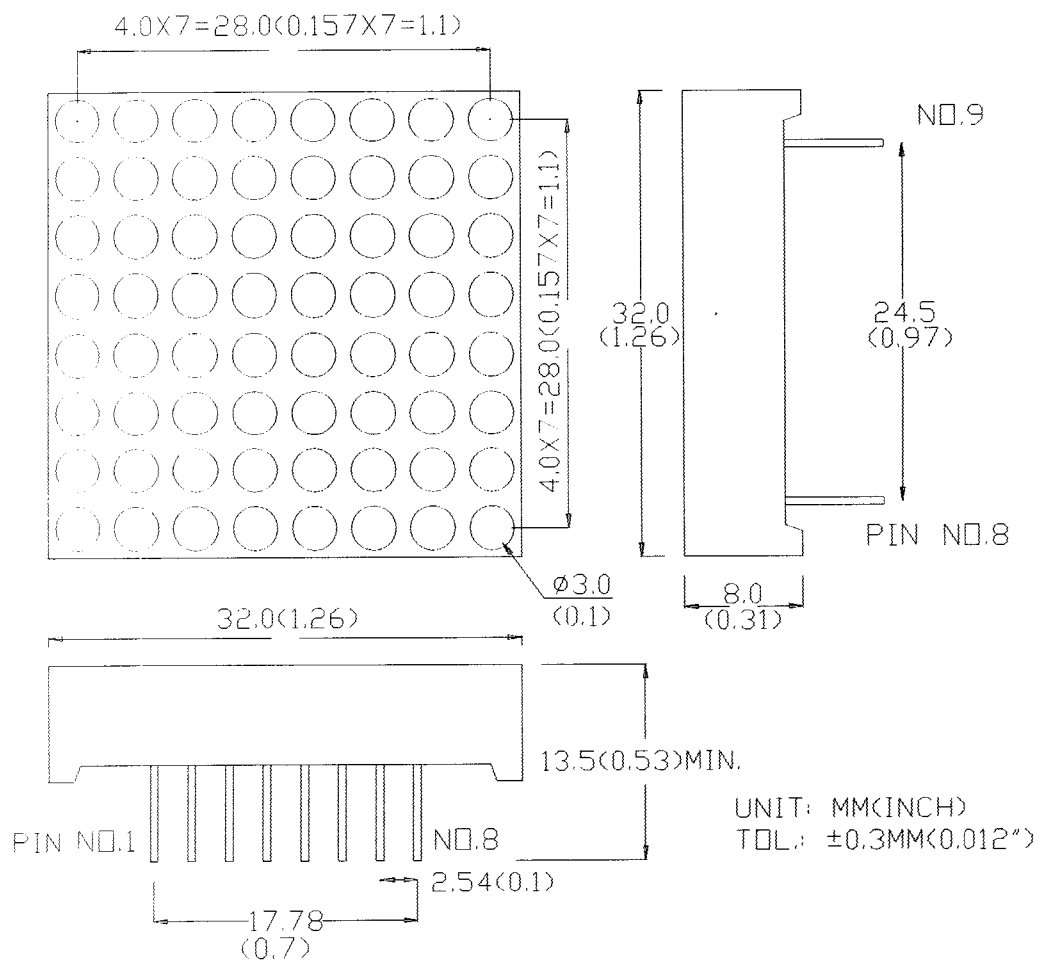
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MECHANICAL OUTLINE:



CIRCUIT DIAGRAM:

